

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2002-261092

(43)Date of publication of application : 13.09.2002

(51)Int.Cl.

H01L 21/316
H01L 21/3205
H01L 21/768

(21)Application number : 2001-052742

(71)Applicant : NEC CORP

(22)Date of filing : 27.02.2001

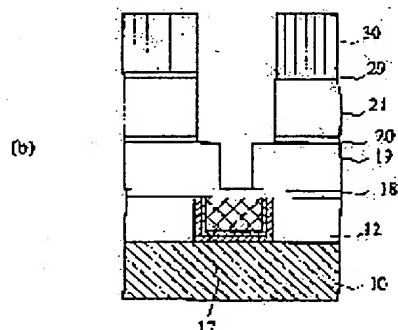
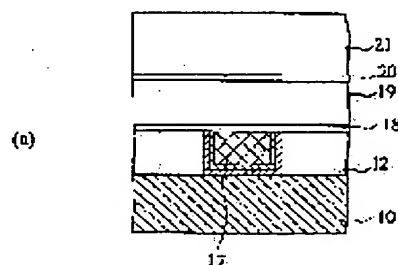
(72)Inventor : SODA EIICHI
TOKASHIKI TAKESHI
NISHIZAWA ATSUSHI
NANBU HIDETAKA

(54) MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To improve interface adhesion between a low dielectric constant film and a protection film without damaging excellent dielectric properties of an organic low dielectric constant material, flatness and gap filling characteristics.

SOLUTION: A resist 30 is removed by ashing employing plasma using mixture gas containing nitrogen and hydrogen. The content of hydrogen in mixture gas is 20% or less in volume base.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

BEST AVAILABLE COPY